

Amendments to the Claims

Claim 1-53 (cancelled).

Claim 54 (currently amended): A method for removing organic ~~materials~~ materials, comprising removing at least a portion of an organic-material-comprising layer from a ~~semiconductive substrate~~ barrier material surface with a pad and a fluid, the fluid being substantially unreactive with the surface and comprising less than or equal to about 0.1 weight percent particles at an initiation of the removing.

Claim 55 (previously presented): The method of claim 54 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist, and polyimide.

Claim 56 (previously presented): The method of claim 54 wherein a pH of the fluid is from about 8 to about 12.

Claim 57 (previously presented): The method of claim 54 wherein the fluid comprises one or both of ammonia and TMAH.

Claim 58 (previously presented): The method of claim 54 wherein the fluid comprises water.

Claim 59-61 (cancelled).

Claim 62 (currently amended): The method of ~~claim 61~~ claim 54 wherein the barrier material comprises one or both of tantalum silicon nitride and tantalum nitride.

Claim 63 (previously presented): The method of claim 54 wherein the pad comprises polyurethane.

Claim 64 (currently amended): ~~The method of claim 54~~ A method for removing organic materials, comprising removing at least a portion of an organic-material-comprising layer from a semiconductive substrate surface with a pad and a fluid, the fluid being substantially unreactive with the surface and comprising less than or equal to about 0.1 weight percent particles at an initiation of the removing, wherein at least some of the particles comprise silica.

Claim 65 (currently amended): ~~The method of claim 54~~ A method for removing organic materials, comprising removing at least a portion of an organic-material-comprising layer from a semiconductive substrate surface with a pad and a fluid, the fluid being substantially unreactive with the surface and comprising less than or equal to about 0.1 weight percent particles at an initiation of the removing, wherein the surface comprises at least two layers, a first conductive layer of the two layers comprising N and Si, and a second conductive layer of the two layers comprising N.

Claim 66-73 (cancelled).

Claim 74 (currently amended): A material removal method ~~comprising~~ comprising:
providing a substrate supporting a ~~conductive-material-comprising~~
barrier-material-comprising layer, the ~~conductive-material-comprising~~
barrier-material-comprising layer having an organic-material-comprising layer thereover;
selectively removing at least a portion of the organic-material-comprising layer
with a first polishing process utilizing a first liquid to thereby expose at least a portion of
an upper surface of the ~~conductive-material-comprising~~ barrier-material-comprising
layer, wherein the first liquid is substantially unreactive with the ~~conductive-material-~~
~~comprising~~ barrier-material-comprising layer and comprises less than or equal to 0.1
weight percent particles at an initiation of the removing; and
removing at least a portion of the ~~conductive-material-comprising~~
barrier-material-comprising layer with a second polishing process utilizing a second
liquid.

Claim 75 (cancelled).

Claim 76 (previously presented): The method of claim 74 wherein the
organic-material-comprising layer comprises one or more of photoresist, non-
photosensitive resist and polyimide.

Claim 77 (previously presented): The method of claim 74 wherein the first polishing
process comprises removing at least a portion of the organic-material-comprising layer
with a chemical mechanical polishing pad and the first liquid.

Claim 78 (currently amended): The method of claim 77 wherein the second polishing process comprises removing at least a portion of the ~~conductive-material-comprising~~ barrier-material-comprising layer with the chemical mechanical polishing pad and the second liquid.

Claim 79 (previously presented): The method of claim 74 wherein the first liquid comprises water.

Claim 80 (previously presented): The method of claim 74 wherein the first liquid comprises one or both of ammonia and TMAH.

Claim 81 (currently amended): The method of claim 74 wherein the second liquid comprises less than or equal to approximately 0.1 weight percent particles at an initiation of the removing of the ~~conductive-material-comprising~~ barrier-material-comprising layer.

Claim 82 (previously presented): The method of claim 74 wherein the second liquid comprises particles.

Claim 83 (previously presented): The method of claim 74 wherein a composition of the second liquid is different than a composition of the first liquid.

Claim 84 (currently amended): ~~The method of claim 74~~ A material removal method comprising:

providing a substrate supporting a conductive-material-comprising layer, the conductive-material-comprising layer having an organic-material-comprising layer thereover;

selectively removing at least a portion of the organic-material-comprising layer with a first polishing process utilizing a first liquid to thereby expose at least a portion of an upper surface of the conductive-material-comprising layer, wherein the first liquid is substantially unreactive with the conductive-material-comprising layer and comprises less than or equal to 0.1 weight percent particles at an initiation of the removing; and

removing at least a portion of the conductive-material-comprising layer with a second polishing process utilizing a second liquid, wherein the second liquid is reactive with the conductive-material-comprising layer.

Claim 85 (cancelled).

Claim 86 (currently amended): The method of claim ~~77~~ 74 wherein the ~~barrier material~~ barrier-material-comprising layer comprises one or both of tantalum silicon nitride and tantalum nitride.

Claim 87 (new): The method of claim 64 wherein the surface comprises a conductive material.

Claim 88 (new): The method of claim 87 wherein the conductive material comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 89 (new): The method of claim 65 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist, and polyimide.

Claim 90 (new): The method of claim 65 wherein a pH of the fluid is from about 8 to about 12.

Claim 91 (new): The method of claim 65 wherein the fluid comprises one or both of ammonia and TMAH.

Claim 92 (new): The method of claim 65 wherein the fluid comprises water.

Claim 93 (new): The method of claim 65 wherein the pad comprises polyurethane.

Claim 94 (new): The method of claim 84 wherein the conductive-material-comprising layer comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 95 (new): The method of claim 84 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist and polyimide.

Claim 96 (new): The method of claim 84 wherein the first polishing process comprises removing at least a portion of the organic-material-comprising layer with a chemical mechanical polishing pad and the first liquid.

Claim 97 (new): The method of claim 96 wherein the second polishing process comprises removing at least a portion of the conductive-material-comprising layer with the chemical mechanical polishing pad and the second liquid.

Claim 98 (new): The method of claim 84 wherein the first liquid comprises water.

Claim 99 (new): The method of claim 84 wherein the first liquid comprises one or both of ammonia and TMAH.

Claim 100 (new): The method of claim 84 wherein the second liquid comprises less than or equal to approximately 0.1 weight percent particles at an initiation of the removing of the conductive-material-comprising layer.

Claim 101 (new): The method of claim 84 wherein a composition of the second liquid is different than a composition of the first liquid.

Claim 102 (new): The method of claim 84 wherein the second liquid comprises particles.